

FQB140N03L / FQI140N03L

30V LOGIC N-Channel MOSFET

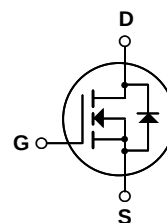
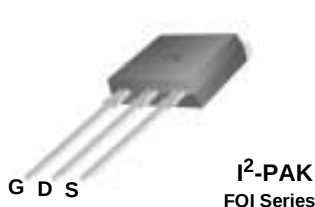
General Description

These N-Channel enhancement mode power field effect transistors are produced using Fairchild's proprietary, planar stripe, DMOS technology.

This advanced technology has been especially tailored to minimize on-state resistance, provide superior switching performance, and withstand high energy pulse in the avalanche and commutation mode. These devices are well suited for low voltage applications such as DC/DC converters, high efficiency switching for power management in portable and battery operated products.

Features

- 140A, 30V, $R_{DS(on)} = 0.0045\Omega$ @ $V_{GS} = 10\text{ V}$
- Low gate charge (typical 73 nC)
- Low C_{rss} (typical 580 pF)
- Fast switching
- 100% avalanche tested
- Improved dv/dt capability
- 175°C maximum junction temperature rating



Absolute Maximum Ratings $T_C = 25^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	FQB140N03L / FQI140N03L	Units
V_{DSS}	Drain-Source Voltage	30	V
I_D	Drain Current - Continuous ($T_C = 25^\circ\text{C}$)	140	A
	- Continuous ($T_C = 100^\circ\text{C}$)	99	A
I_{DM}	Drain Current - Pulsed (Note 1)	490	A
V_{GSS}	Gate-Source Voltage	± 20	V
E_{AS}	Single Pulsed Avalanche Energy (Note 2)	710	mJ
I_{AR}	Avalanche Current (Note 1)	140	A
E_{AR}	Repetitive Avalanche Energy (Note 1)	18.0	mJ
dv/dt	Peak Diode Recovery dv/dt (Note 3)	7.0	V/ns
P_D	Power Dissipation ($T_A = 25^\circ\text{C}$) *	3.75	W
	Power Dissipation ($T_C = 25^\circ\text{C}$)	180	W
	- Derate above 25°C	1.2	W/ $^\circ\text{C}$
T_J, T_{STG}	Operating and Storage Temperature Range	-55 to +175	$^\circ\text{C}$
T_L	Maximum lead temperature for soldering purposes, 1/8" from case for 5 seconds	300	$^\circ\text{C}$

Thermal Characteristics

Symbol	Parameter	Typ	Max	Units
$R_{\theta JC}$	Thermal Resistance, Junction-to-Case	--	0.84	$^\circ\text{C/W}$
$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient *	--	40	$^\circ\text{C/W}$
$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient	--	62.5	$^\circ\text{C/W}$

* When mounted on the minimum pad size recommended (PCB Mount)

Electrical Characteristics $T_C = 25^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	Test Conditions	Min	Typ	Max	Units
--------	-----------	-----------------	-----	-----	-----	-------

Off Characteristics

BV_{DSS}	Drain-Source Breakdown Voltage	$V_{GS} = 0\text{ V}, I_D = 250\mu\text{ A}$	30	--	--	V
$\Delta BV_{DSS} / \Delta T_J$	Breakdown Voltage Temperature Coefficient	$I_D = 250\mu\text{ A}$, Referenced to 25°C	--	0.03	--	V/ $^\circ\text{C}$
I_{DSS}	Zero Gate Voltage Drain Current	$V_{DS} = 30\text{ V}, V_{GS} = 0\text{ V}$	--	--	1	μA
		$V_{DS} = 24\text{ V}, T_C = 150^\circ\text{C}$	--	--	10	μA
I_{GSSF}	Gate-Body Leakage Current, Forward	$V_{GS} = 20\text{ V}, V_{DS} = 0\text{ V}$	--	--	100	nA
I_{GSSR}	Gate-Body Leakage Current, Reverse	$V_{GS} = -20\text{ V}, V_{DS} = 0\text{ V}$	--	--	-100	nA

On Characteristics

$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS} = V_{GS}, I_D = 250\mu\text{ A}$	1.0	--	2.5	V
$R_{DS(on)}$	Static Drain-Source On-Resistance	$V_{GS} = 10\text{ V}, I_D = 70\text{ A}$	--	0.0038	0.0045	Ω
		$V_{GS} = 5\text{ V}, I_D = 70\text{ A}$	--	0.005	0.006	Ω
g_{FS}	Forward Transconductance	$V_{DS} = 15\text{ V}, I_D = 70\text{ A}$ (Note 4)	--	85	--	S

Dynamic Characteristics

C_{iss}	Input Capacitance	$V_{DS} = 25\text{ V}, V_{GS} = 0\text{ V},$ $f = 1.0\text{ MHz}$	--	3400	4420	pF
C_{oss}	Output Capacitance		--	2090	2720	pF
C_{rss}	Reverse Transfer Capacitance		--	580	755	pF

Switching Characteristics

$t_{d(on)}$	Turn-On Delay Time	$V_{DD} = 15\text{ V}, I_D = 70\text{ A},$ $R_G = 25\Omega$ (Note 4, 5)	--	60	130	ns
t_r	Turn-On Rise Time		--	770	1500	ns
$t_{d(off)}$	Turn-Off Delay Time		--	25	60	ns
t_f	Turn-Off Fall Time		--	250	510	ns
Q_g	Total Gate Charge	$V_{DS} = 24\text{ V}, I_D = 140\text{ A},$ $V_{GS} = 5\text{ V}$ (Note 4, 5)	--	73	95	nC
Q_{gs}	Gate-Source Charge		--	29.5	--	nC
Q_{gd}	Gate-Drain Charge		--	38.5	--	nC

Drain-Source Diode Characteristics and Maximum Ratings

I _S	Maximum Continuous Drain-Source Diode Forward Current		--	--	140	A
I _{SM}	Maximum Pulsed Drain-Source Diode Forward Current		--	--	490	A
V _{SD}	Drain-Source Diode Forward Voltage	V _{GS} = 0 V, I _S = 140 A	--	--	1.5	V
t _{rr}	Reverse Recovery Time	V _{GS} = 0 V, I _S = 140 A,	--	70	--	ns
Q _{rr}	Reverse Recovery Charge	dI _F / dt = 100 A/μs (Note 4)	--	105	--	nC

Notes:

1. Repetitive Rating : Pulse width limited by maximum junction temperature
2. $L = 36\mu\text{H}$, $I_{AS} = 140\text{ A}$, $V_{DD} = 15\text{ V}$, $R_G = 25\Omega$, Starting $T_J = 25^\circ\text{C}$
3. $I_{SD} \leq 140\text{ A}$, $dI/dt \leq 300\text{ A}/\mu\text{s}$, $V_{DD} \leq BV_{DSS}$, Starting $T_J = 25^\circ\text{C}$
4. Pulse Test : Pulse width $\leq 300\mu\text{s}$, Duty cycle $\leq 2\%$
5. Essentially independent of operating temperature
6. Continuous Drain Current Calculated by Maximum Junction Temperature : Limited by Package

Typical Characteristics

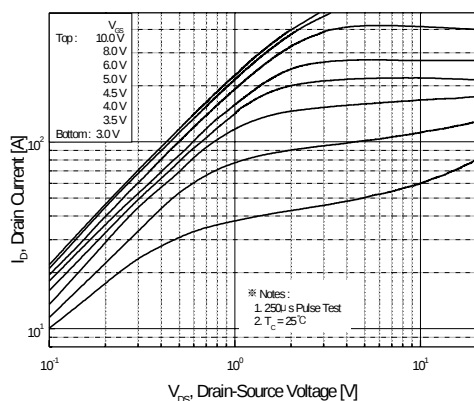


Figure 1. On-Region Characteristics

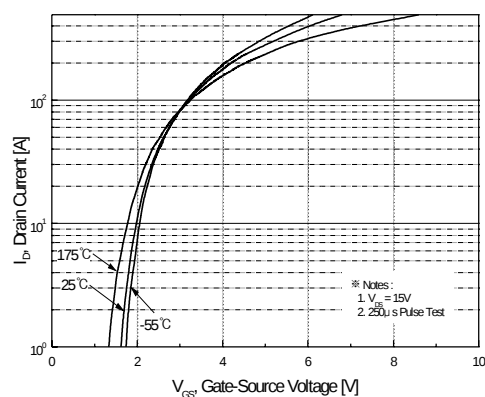


Figure 2. Transfer Characteristics

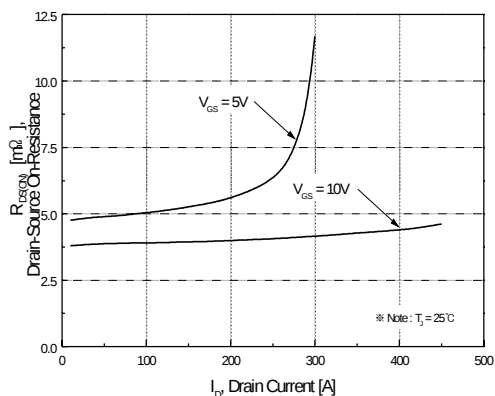


Figure 3. On-Resistance Variation vs. Drain Current and Gate Voltage

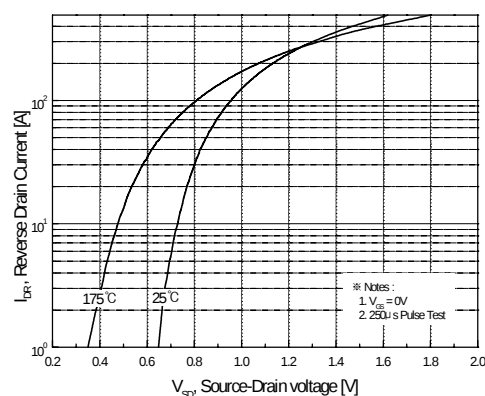


Figure 4. Body Diode Forward Voltage Variation vs. Source Current and Temperature

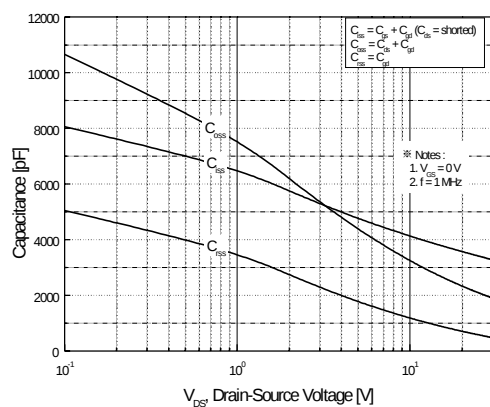


Figure 5. Capacitance Characteristics

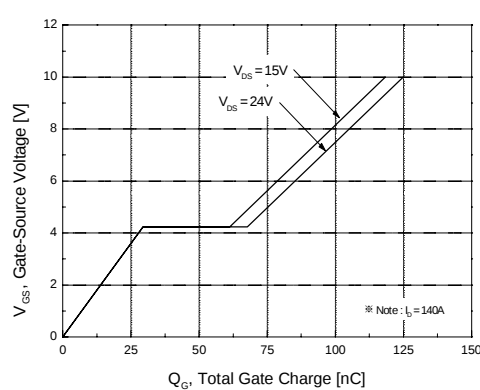


Figure 6. Gate Charge Characteristics

Typical Characteristics (Continued)

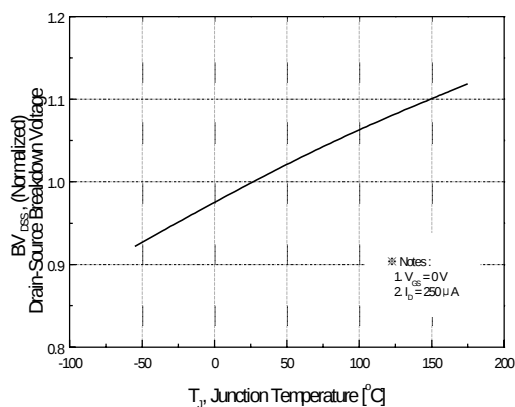


Figure 7. Breakdown Voltage Variation vs. Temperature

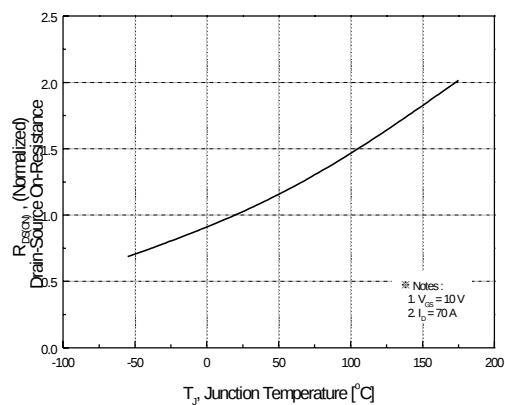


Figure 8. On-Resistance Variation vs. Temperature

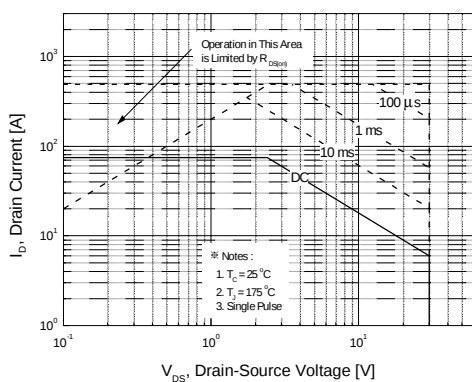


Figure 9. Maximum Safe Operating Area

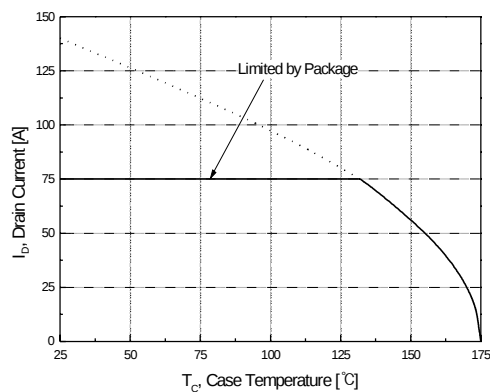


Figure 10. Maximum Drain Current vs. Case Temperature

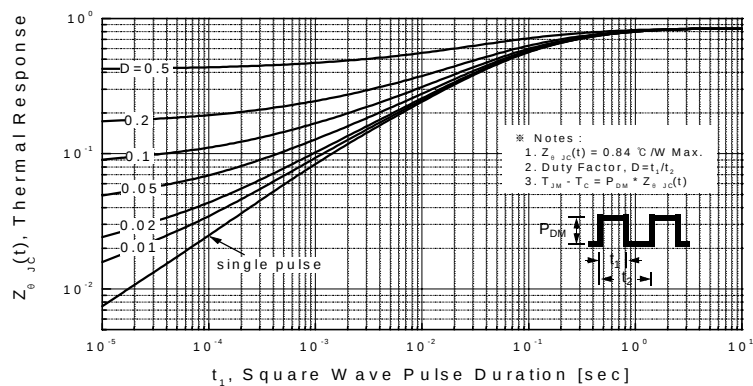
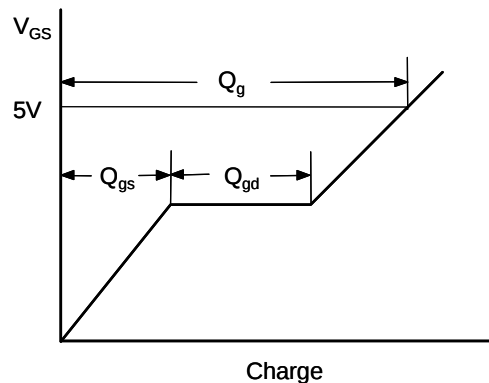
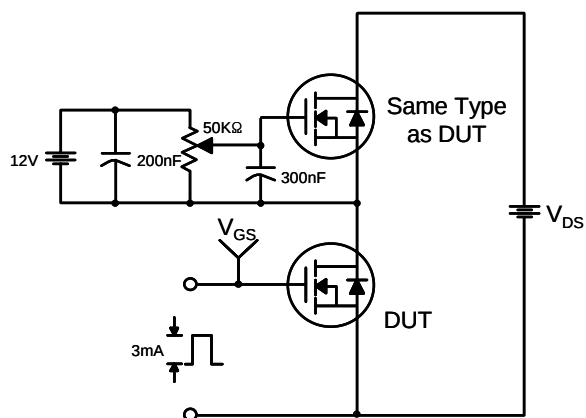
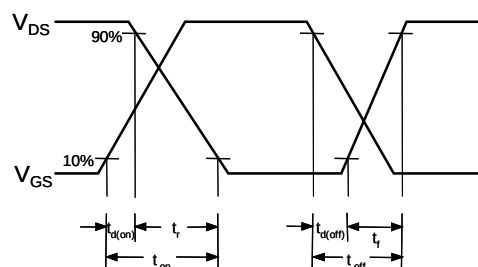
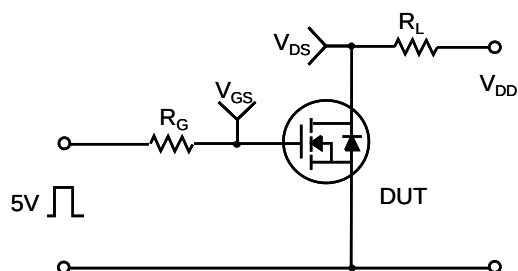


Figure 11. Transient Thermal Response Curve

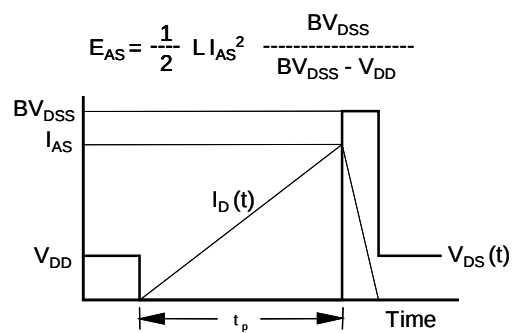
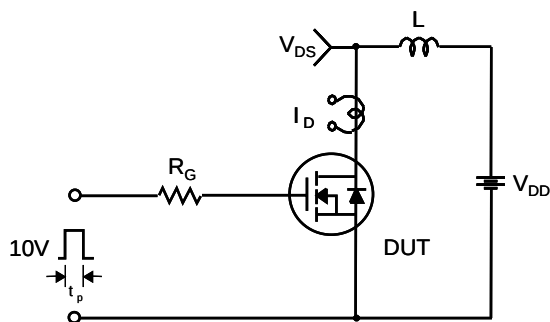
Gate Charge Test Circuit & Waveform



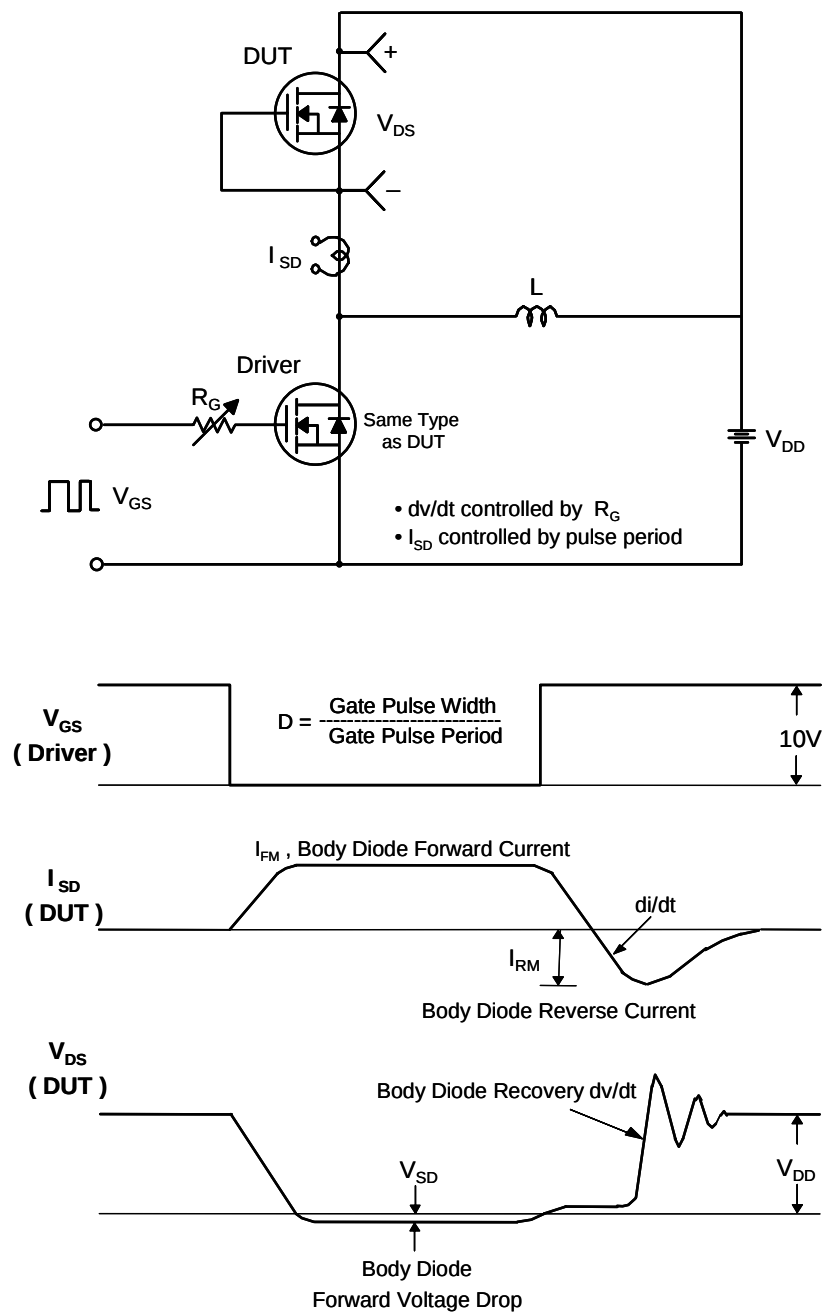
Resistive Switching Test Circuit & Waveforms



Unclamped Inductive Switching Test Circuit & Waveforms



Peak Diode Recovery dv/dt Test Circuit & Waveforms



FQ1140N03L / FQ1140N03L

Technical drawing of a 10-pin D-sub connector showing front, side, and top views with dimensions in millimeters.

Front View (Top Left):

- Overall width: 9.90 ± 0.20
- Overall height: 15.30 ± 0.30
- Pin height (from base): 4.90 ± 0.20
- Pin pitch: 2.54 TYP
- Pin diameter: 0.80 ± 0.10
- Pin length (from base): 1.27 ± 0.10
- Pin spacing (from center): 1.40 ± 0.20
- Pin diameter (from center): 1.20 ± 0.20
- Pin diameter (from center): 0.40

Side View (Top Right):

- Overall width: 4.50 ± 0.20
- Overall height: 2.54 ± 0.30
- Pin height (from base): 2.00 ± 0.10
- Pin pitch: 2.54 TYP
- Pin diameter: 0.80 ± 0.10
- Pin length (from base): 1.27 ± 0.10
- Pin spacing (from center): 1.40 ± 0.20
- Pin diameter (from center): 1.20 ± 0.20
- Pin diameter (from center): 0.40

Top View (Bottom Left):

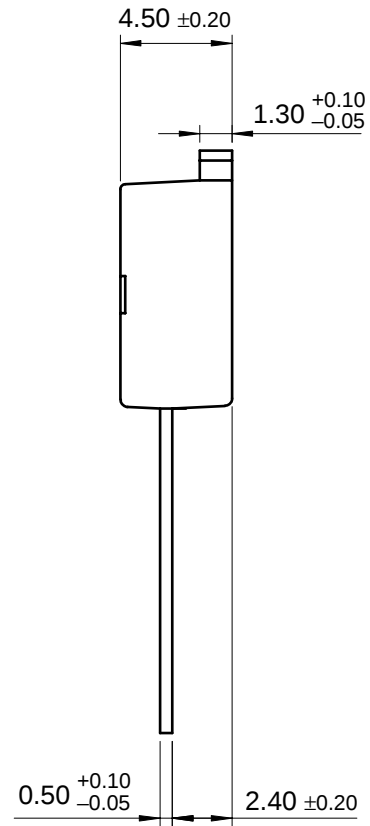
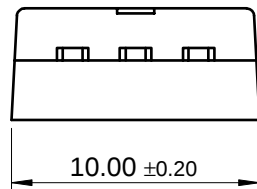
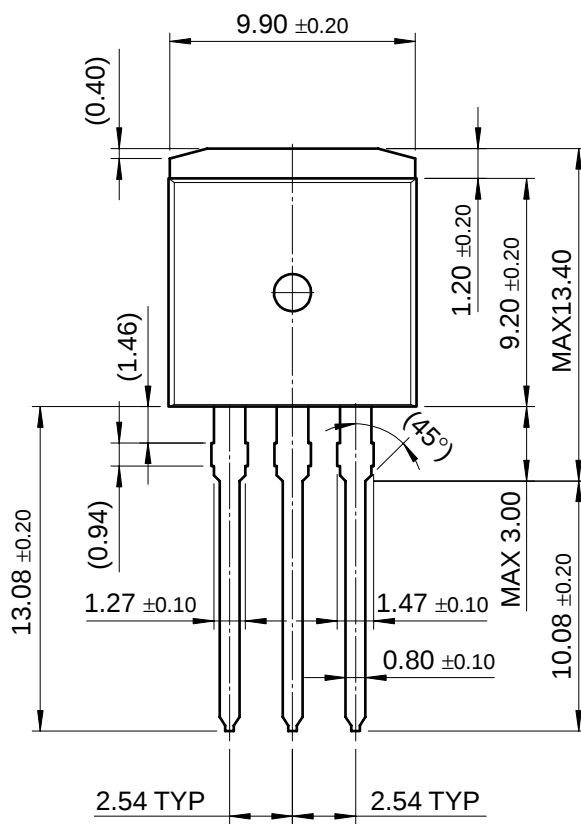
- Overall width: 10.00 ± 0.20

Bottom View (Bottom Right):

- Overall width: 10.00 ± 0.20
- Overall height: 15.30 ± 0.30
- Pin height (from base): 4.90 ± 0.20
- Pin pitch: 2.54 TYP
- Pin diameter: 0.80 ± 0.10
- Pin length (from base): 1.27 ± 0.10
- Pin spacing (from center): 1.40 ± 0.20
- Pin diameter (from center): 1.20 ± 0.20
- Pin diameter (from center): 0.40

Package Dimensions (Continued)

I²PAK



FQB140N03L / FQI140N03L

TRADEMARKS

The following are registered and unregistered trademarks Fairchild Semiconductor owns or is authorized to use and is not intended to be an exhaustive list of all such trademarks.

ACE ^x TM	FAST [®]	OPTOPLANAR TM	SuperSOT TM -3
Bottomless TM	FAST ^r TM	PACMAN TM	SuperSOT TM -6
CoolFET TM	FRFET TM	POP TM	SuperSOT TM -8
CROSSVOLT TM	GlobalOptoisolator TM	PowerTrench [®]	SyncFET TM
DenseTrench TM	GTO TM	QFET TM	TinyLogic TM
DO TM	HiSeC TM	QS TM	UHC TM
EcoSPARK TM	ISOPPLANAR TM	QT Optoelectronics TM	UltraFET [®]
E ² CMOS TM	LittleFET TM	Quiet Series TM	VCX TM
EnSigna TM	MicroFET TM	SLIENT SWITCHER [®]	
FACT TM	MICROWIRE TM	SMART START TM	
FACT Quiet Series TM	OPTOLOGIC TM	Stealth TM	

DISCLAIMER

FAIRCHILD SEMICONDUCTOR RESERVES THE RIGHT TO MAKE CHANGES WITHOUT FURTHER NOTICE TO ANY PRODUCTS HEREIN TO IMPROVE RELIABILITY, FUNCTION OR DESIGN. FAIRCHILD DOES NOT ASSUME ANY LIABILITY ARISING OUT OF THE APPLICATION OR USE OF ANY PRODUCT OR CIRCUIT DESCRIBED HEREIN; NEITHER DOES IT CONVEY ANY LICENSE UNDER ITS PATENT RIGHTS, NOR THE RIGHTS OF OTHERS.

LIFE SUPPORT POLICY

FAIRCHILD'S PRODUCTS ARE NOT AUTHORIZED FOR USE AS CRITICAL COMPONENTS IN LIFE SUPPORT DEVICES OR SYSTEMS WITHOUT THE EXPRESS WRITTEN APPROVAL OF FAIRCHILD SEMICONDUCTOR CORPORATION.

As used herein:

1. Life support devices or systems are devices or systems which, (a) are intended for surgical implant into the body, or (b) support or sustain life, or (c) whose failure to perform when properly used in accordance with instructions for use provided in the labeling, can be reasonably expected to result in significant injury to the user.
2. A critical component is any component of a life support device or system whose failure to perform can be reasonably expected to cause the failure of the life support device or system, or to affect its safety or effectiveness.

PRODUCT STATUS DEFINITIONS

Definition of Terms

Datasheet Identification	Product Status	Definition
Advance Information	Formative or In Design	This datasheet contains the design specifications for product development. Specifications may change in any manner without notice.
Preliminary	First Production	This datasheet contains preliminary data, and supplementary data will be published at a later date. Fairchild Semiconductor reserves the right to make changes at any time without notice in order to improve design.
No Identification Needed	Full Production	This datasheet contains final specifications. Fairchild Semiconductor reserves the right to make changes at any time without notice in order to improve design.
Obsolete	Not In Production	This datasheet contains specifications on a product that has been discontinued by Fairchild semiconductor. The datasheet is printed for reference information only.

Данный компонент на территории Российской Федерации

Вы можете приобрести в компании MosChip.

Для оперативного оформления запроса Вам необходимо перейти по данной ссылке:

<http://moschip.ru/get-element>

Вы можете разместить у нас заказ для любого Вашего проекта, будь то серийное производство или разработка единичного прибора.

В нашем ассортименте представлены ведущие мировые производители активных и пассивных электронных компонентов.

Нашей специализацией является поставка электронной компонентной базы двойного назначения, продукции таких производителей как XILINX, Intel (ex.ALTERA), Vicor, Microchip, Texas Instruments, Analog Devices, Mini-Circuits, Amphenol, Glenair.

Сотрудничество с глобальными дистрибьюторами электронных компонентов, предоставляет возможность заказывать и получать с международных складов практически любой перечень компонентов в оптимальные для Вас сроки.

На всех этапах разработки и производства наши партнеры могут получить квалифицированную поддержку опытных инженеров.

Система менеджмента качества компании отвечает требованиям в соответствии с ГОСТ Р ИСО 9001, ГОСТ РВ 0015-002 и ЭС РД 009

Офис по работе с юридическими лицами:

105318, г.Москва, ул.Щербаковская д.3, офис 1107, 1118, ДЦ «Щербаковский»

Телефон: +7 495 668-12-70 (многоканальный)

Факс: +7 495 668-12-70 (доб.304)

E-mail: info@moschip.ru

Skype отдела продаж:

moschip.ru

moschip.ru_4

moschip.ru_6

moschip.ru_9